



<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)	<b>ATTY. DOCKET NO.</b> 43890-673	<b>SERIAL NO.</b> 10/812,416
	<b>APPLICANT</b> Tetsuzo UEDA, et al.	
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**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US			
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**FOREIGN PATENT DOCUMENTS**

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**OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
SWC     SWC		ONOJIMA, Norio., et al. "Growth of AlN (1120) on 6HSiC (1120) by Molecular Epitaxy." Jpn J. Appl. Phys. Vol. 41 (2002) pp. L 1348-1350
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		N. ONOJIMA., et al. "Extended Abstract of 2003 Fall Meeting of the Japan Society of Applied Physics Society, 30p-G-10
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EXAMINER <div style="font-size: 1.5em; font-family: cursive;">CRANE</div>	DATE CONSIDERED <div style="font-size: 1.5em; font-family: cursive;">10/2005</div>
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